

Features

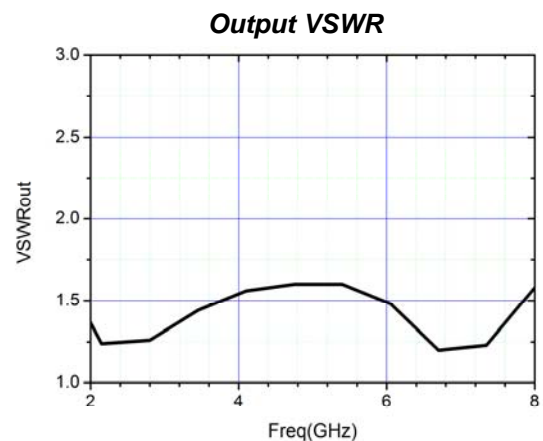
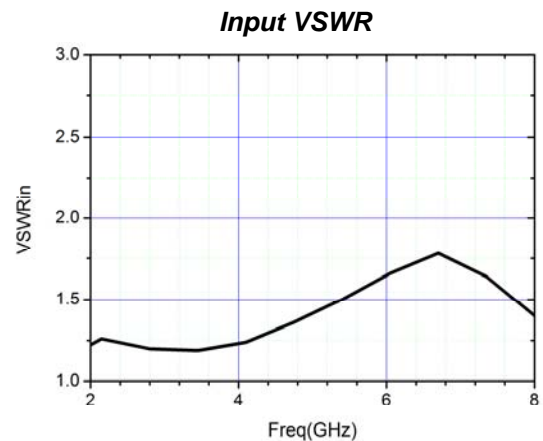
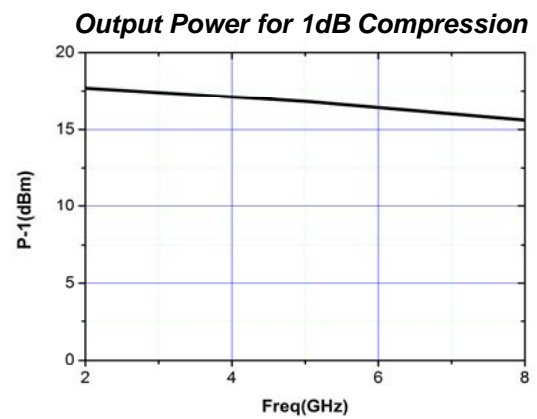
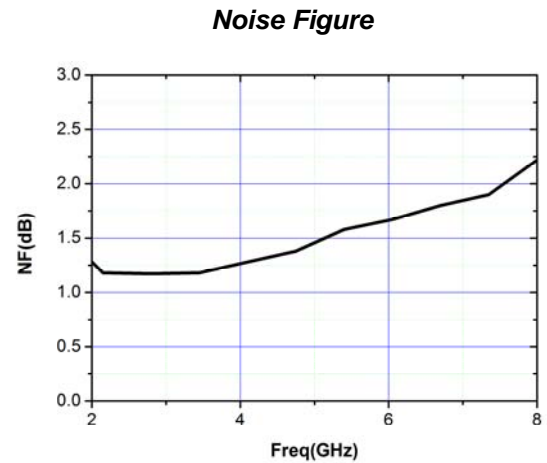
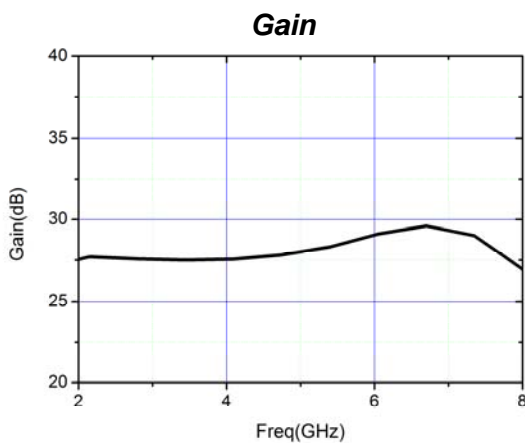
Freq: 2~8GHz
 Gain: 28.5dB
 Noise Figure: 1.8dB
 Output Power for 1 dB Compression: 16.5dBm
 Supply Voltage: +5V
 Supply Current: 85mA
 Chip Size: 1.4mm×1.25mm×0.1mm

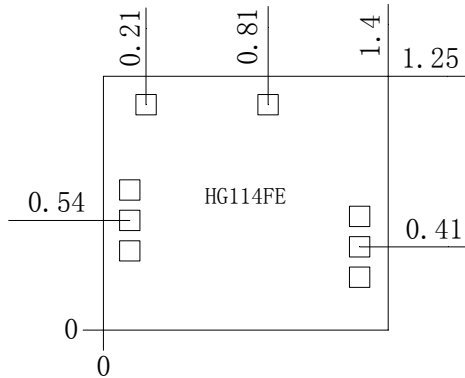
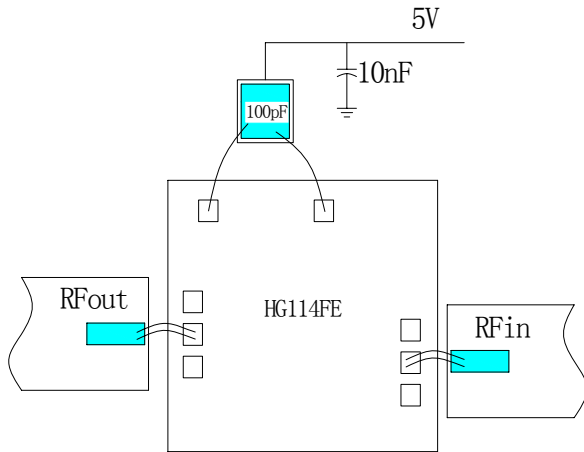
General Description

The HG114FE is a GaAs pHEMT MMIC Low Noise Amplifier operating between 2 and 8GHz. The LNA has been optimized to provide 28.5dB gain, 1.8dB noise figure and 16.5dBm output power for 1dB compression.

Electrical Specifications ($T_A=25^\circ\text{C}$, $V_{dd}=+5\text{V}$).

Parameter	Min.	Typ.	Max.
Freq(GHz)	2~8		
Gain (dB)	—	28.5	—
Gain Flatness (dB)	—	±1.3	—
Input VSWR	—	1.5	—
Output VSWR	—	1.5	—
Noise Figure(dB)	—	1.8	—
Output Power for 1 dB Compression(dBm)	—	16.5	—

Measured Performance


Outline Drawing (mm)

Assembly Diagram

Absolute Maximum Ratings

Supply Voltage	+5.5V
RF Input Power	+18dBm
Operating Temperature	-55°C ~ 125°C
Storage Temperature	-65°C ~ 150°C

Notes:

1. The chip should be stored in a dry and nitrogen environment, and used in a clean environment.
2. GaAs material is brittle, can not touch the surface of the chip, must be careful when using.
3. The chip is welding with conductive adhesive or alloy (alloy temperature should not exceed 300°C, and no more than 30 sec.), and should make it fully grounded.
4. The chip microwave port and substrate gap is not exceeding 0.05mm, with $\Phi 25\mu\text{m}$ double gold wire bonding, suggested length of gold wire 250~400 μm .
5. Chip microwave port with a DC blocking capacitor.
6. The chip is sensitive to static electricity, and should be protected against static electricity during storage and use.